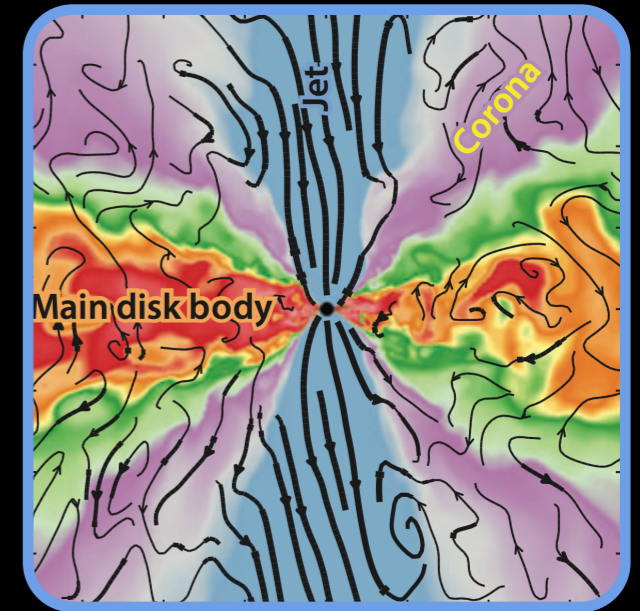


Electron and Proton Heating in Transrelativistic Magnetic Reconnection

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- ▶ Transrelativistic reconnection: $\sigma_w \equiv B_0^2/4\pi w \sim 0.1 - 1$ (w is enthalpy density)
 - ▶ Corona of Sgr A*
 - ▶ Microphysics: unresolved in MHD
 - ▶ Reconnection: important effect
 - ▶ Should Include to model EHT observations
- ▶ How much magnetic energy is dissipated to electrons, protons?
 - ▶ Particle in cell simulations: **TRISTAN-MP**
 - ▶ 2D in space, but track all 3 components of momentum
- ▶ Main focus: electron heating (rather than acceleration)
 - ▶ How does the energy partition vary with inflow parameters, in the transrelativistic regime?



Yuan + Narayan 2014

Beta (of the ions)

$$\beta_i = \frac{n_i k_B T_i}{B^2 / (8\pi)} = \frac{\text{thermal pressure}}{\text{magnetic pressure}}$$

0.01 - 2

Sigma (magnetization)

$$\sigma_w = \frac{B^2 / 4\pi}{w} = \frac{\text{magnetic pressure} (\times 2)}{\text{enthalpy density}}$$

0.1 - 10

Temperature ratio

$$\frac{T_e}{T_i} = \frac{\text{electron temperature}}{\text{ion temperature}}$$

0.1 - 1

Mass ratio

$$\frac{m_i}{m_e} = \frac{\text{Ion mass}}{\text{Electron mass}}$$

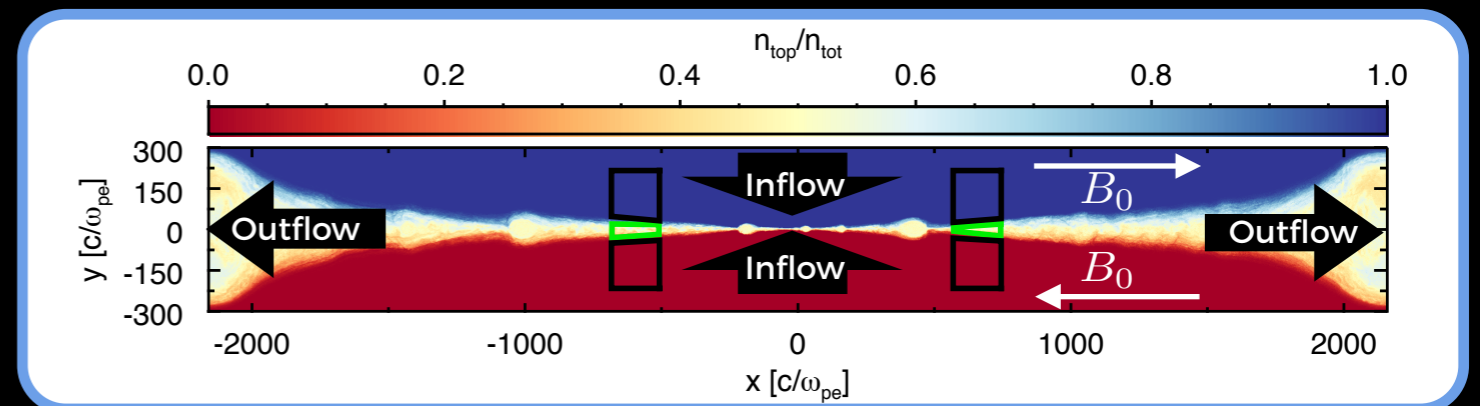
10 - 1836

- ▶ Here, we focus on antiparallel reconnection (no guide field)

- ▶ Characterize heating via dimensionless ratio (as in Drake et al. 2014)

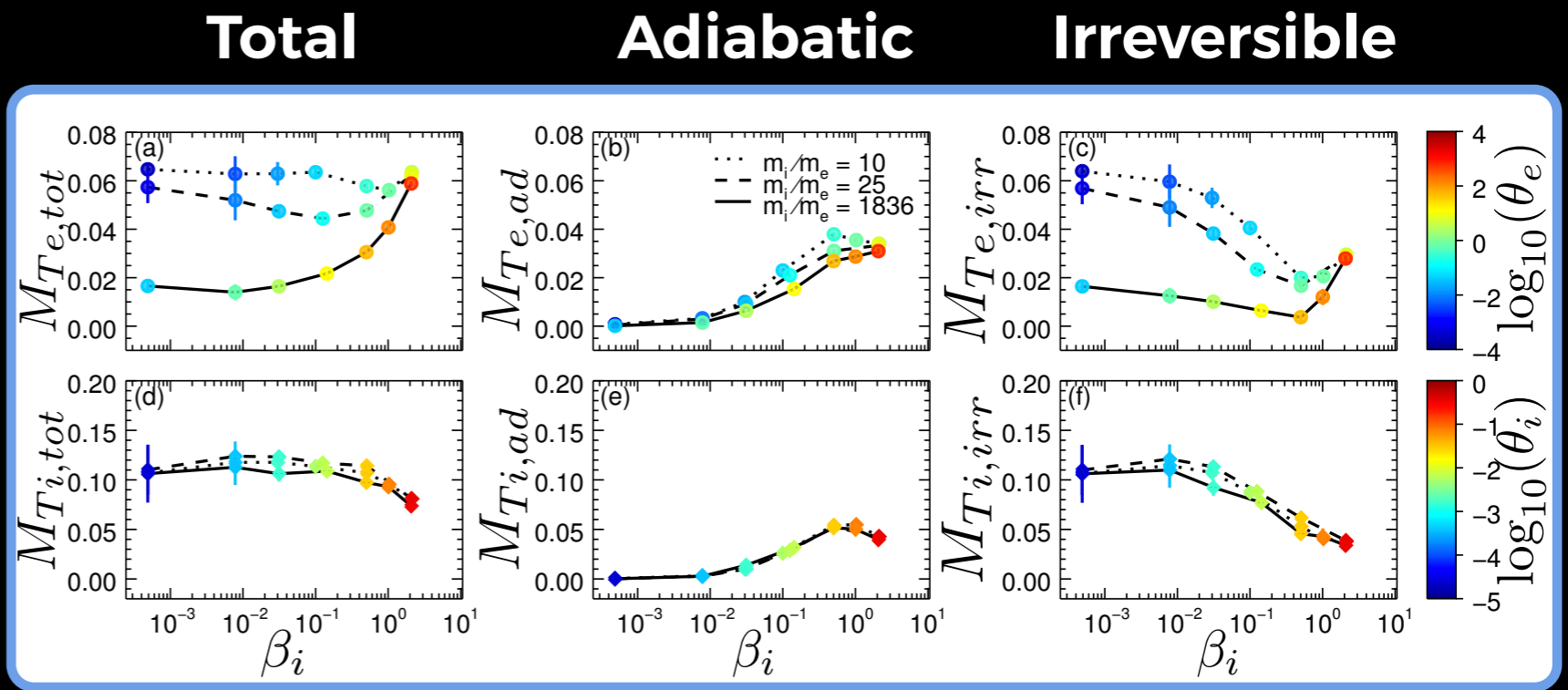
$$M_{Te} = \frac{k_B T_{e,out} - k_B T_{e,in}}{B^2 / 4\pi n}$$

- ▶ We further separate heating into irreversible and adiabatic components



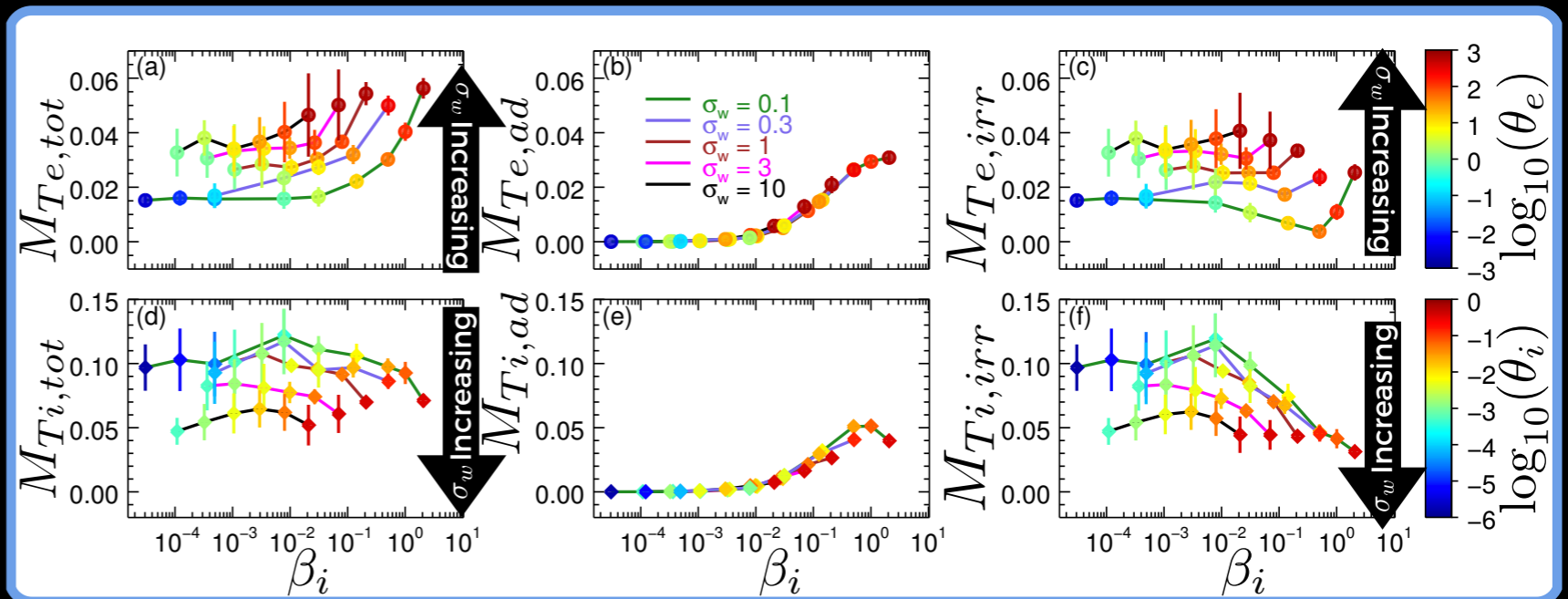
Mass ratio

- At low β_i , electron heating depends on mass ratio, m_i/m_e
- Mass ratio ranges from 10 - 1836



Magnetization

- vary σ_w from 0.1 - 10
- Here, $m_i/m_e = 1836$ and $T_e/T_i = 1$
- At high β_i , total electron heating attains a value of $M_{Te,tot} \approx 0.05 \approx M_{Ti,tot}$
- σ_w dependent plateau at low β_i , with higher magnetizations giving larger heating efficiency



Energy equipartition

- Achieve by increasing β_i (at fixed σ_w), or by increasing σ_w (at fixed β_i)
- In either case, ratio of ion to elec. skin-depth $\rightarrow 1$ in the downstream
- In panels (a) and (b), points indicate simulations, lines are fit: $q_{ue,fit} = 0.5 \exp \left[-\left(1 - \beta_i/\beta_{i,max}\right)^{3.3} / \left(1 + 1.2\sigma_w^{0.7}\right) \right]$, where $\beta_{i,max} = 1/4\sigma_w$

